

cont. SUB DI 7
5 a gate electrode located on the insulator substrate;

a gate insulator film provided above the insulator substrate and the gate electrode; and

a polycrystalline silicon film located on the gate insulator film,

cont C1
10 the gate electrode having a center portion with a flat surface and a pair of tapered end portions with inclined surfaces, an angle between each of the inclined surfaces of the pair of tapered end portions and a surface of the insulator substrate being set within a range of 10° to 40° so that a uniform grain size of the polycrystalline silicon film is acquired above the center portion and the pair of tapered end portions, a gate withstand voltage of the thin film transistor is secured, and the inclined surfaces of the pair of tapered end portions are prevented from increasing.

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